TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type (darlington power transistor 4 in 1)

# MP4025

High Power Switching Applications

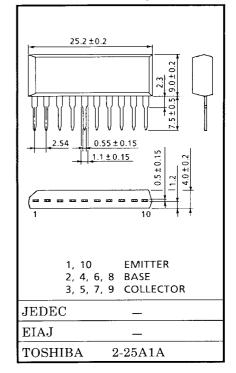
Hammer Drive, Pulse Motor Drive and Inductive Load Switching

- Small package by full molding (SIP 10 pin)
- Built-in resistance (RB).
- Surge voltage is clamped by zener diode (C-B).
- Low V<sub>CE</sub> (sat): V<sub>CE</sub> (sat) = 1.2 V (max) (I<sub>C</sub> = 0.5 A, V<sub>BH</sub> = 4.2 V)
- High DC current gain:  $h_{FE} = 2000 \text{ (min)} (V_{CE} = 2 \text{ V}, I_{C} = 0.7 \text{ A})$

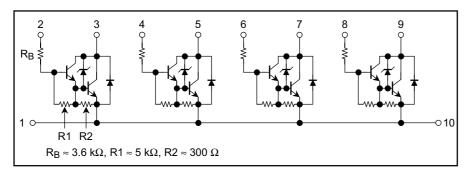
## Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	50	V	
Collector-emitter voltage		V <sub>CEO</sub>	60 ± 10	V	
Emitter-base voltage		V <sub>EBO</sub>	6	V	
Input voltage		VB	20	V	
Collector current	DC	Ι <sub>C</sub>	1.5	A	
	Pulse	I <sub>CP</sub>	2.0		
Collector power dissipation (1 device operation)		P <sub>C</sub>	2.0	W	
Collector power dissipation (4 devices operation)		Ρ <sub>T</sub>	4.0	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

#### INDUSTRIAL APPLICATIONS Unit in mm



# Array Configuration



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## **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance of junction to ambient (4 devices operation, $Ta = 25^{\circ}C$ )		31.3	°C/W
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)		260	°C

# **Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I <sub>CBO</sub>	$V_{CB} = 45 \text{ V}, I_{E} = 0$	_		10	μΑ	
Collector cut-off current		I <sub>CEO</sub>	$V_{CE} = 45 \text{ V}, \text{ I}_{B} = 0$			10	μA	
Emitter cut-off cu	rrent	I <sub>EBO</sub>	$V_{EB} = 6 V, I_{C} = 0$	0.46	_	1.25	mA	
Collector-emitter breakdown voltage		V (BR) CEO	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	50	60	70	V	
Resistance		R <sub>B</sub>	—	2.5	3.6	4.7	kΩ	
DC current gain		h <sub>FE</sub>	$V_{CE} = 2 V, I_{C} = 0.7 A$	2000			_	
Collector-emitter saturation voltage		V <sub>CE (sat) (1)</sub>	$I_{C} = 0.5 \text{ A}, V_{BH} = 4.2 \text{ V}$			1.2	V	
		V <sub>CE (sat)</sub> (2)	$I_{C} = 0.7 \text{ A}, V_{BH} = 9 \text{ V}$	_		1.5		
Input voltage (low)		V <sub>BL</sub>	$V_{CE} = 30 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}$			0.7	V	
Switching time	Turn-on time	t <sub>on</sub>	Input $20 \ \mu s$ $V_{BH} = 5 \ V$ Duty cycle $\leq 1\%$	_	0.3	_	μs	
	Storage time	t <sub>stg</sub>		_	4.0	_		
	Fall time	t <sub>f</sub>		—	0.6	_		

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